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April 1999

FDS6630A

FAIRCHILD SEMICONDUCTOR

FDS6630A N-Channel Logic Level PowerTrench[™] MOSFET

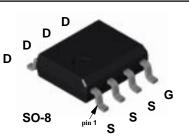
General Description

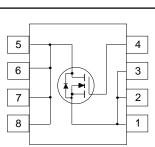
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Applications

- DC/DC converter
- Load switch
- Motor drives





• 6.5 A, 30 V. $R_{DS(on)} = 0.038 \Omega @ V_{GS} = 10 V$

• High performance trench technology for extremely

• High power and current handling capability.

• Low gate charge (5nC typical).

• Fast switching speed.

low R_{DS(ON)}.

 $R_{DS(on)} = 0.053 \ \Omega \ @ V_{GS} = 4.5 \ V$

Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 20	V
I _D	Drain Current - Continuous	(Note 1a)	6.5	А
	- Pulsed		40	
P _D Power	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	∘C

Features

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	∘C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS6630A	FDS6630A	13"	12mm	2500 units

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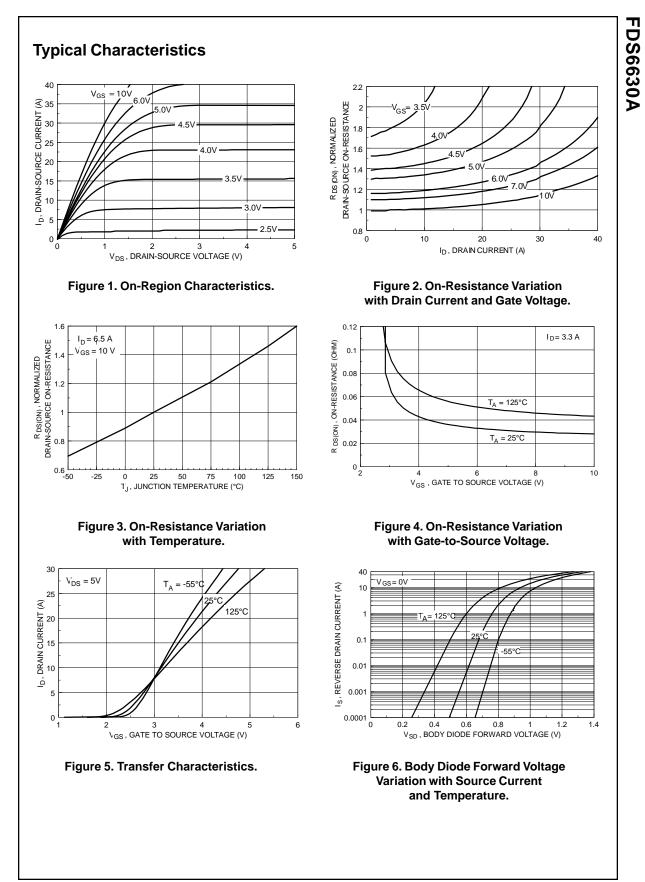
Acteristics Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ $I_D = 250 \mu\text{A}, \text{ Referenced to } 25^{\circ}\text{C}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	30	24		V mV/∘C
Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward	I_D = 250 μ A, Referenced to 25°C V_{DS} = 24 V, V_{GS} = 0 V	30	24		-
Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward	V _{DS} = 24 V, V _{GS} = 0 V		24		mV/∘C
Gate-Body Leakage Current, Forward					
	$V_{00} = 20 V V_{00} = 0 V$			1	μA
Gate-Body Leakage Current Reverse	$v_{GS} = 20 v_1, v_{DS} = 0 v_1$			100	nA
Cale-Douy Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
acteristics (Note 2)					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	1.7	3	V
Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		-4		mV/∘C
Static Drain-Source On-Resistance	$ \begin{array}{l} V_{GS} = 10 \ V, \ I_D = 6.5 \ A \\ V_{GS} = 10 \ V, \ I_D = 6.5 \ A, \ T_J \!=\! 125^\circ C \\ V_{GS} = 4.5 \ V, \ I_D = 5.5 \ A \end{array} $		0.028 0.044 0.040	0.038 0.060 0.053	Ω
On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	20			А
Forward Transconductance	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$		13		S
Characteristics					
	$V_{DS} = 15 V. V_{GS} = 0 V.$		460		pF
	f = 1.0 MHz		115		pF
					pF
•					
	$V_{} = 15 V_{} = 1.6$		5	11	ns
,			-		ns
	1		-		ns
,	-			-	ns
	$V_{} = 5 V_{} = 6 5 A_{}$		-		nC
Gate-Source Charge	$V_{\rm DS} = 5 V$, $V_{\rm B} = 0.3 A$, $V_{\rm GS} = 5 V$		2	,	nC
Oate Oodice Onlarge	4		0.9		nC
Gate-Drain Charge					
Gate-Drain Charge					
urce Diode Characteristics an	-				
	-			2.1	A
	Gate Threshold Voltage Gate Threshold Voltage Temperature Coefficient Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics Input Capacitance Qutput Capacitance Reverse Transfer Capacitance gCharacteristics (Note 2) Turn-On Delay Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge	Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ Gate Threshold Voltage $I_D = 250 \ \mu A$, Referenced to $25 \circ C$ Temperature Coefficient $I_D = 250 \ \mu A$, Referenced to $25 \circ C$ Static Drain-Source $V_{GS} = 10 \ V$, $I_D = 6.5 \ A$ On-Resistance $V_{GS} = 10 \ V$, $I_D = 6.5 \ A$ On-State Drain Current $V_{GS} = 10 \ V$, $V_{DS} = 5 \ V$ Forward Transconductance $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$ Characteristics Input CapacitanceInput Capacitance $V_{DS} = 15 \ V$, $V_{GS} = 0 \ V$, f = 1.0 MHz Characteristics (Note 2)Turn-On Delay Time $V_{DS} = 15 \ V$, $I_D = 1 \ A$, $V_{GS} = 10 \ V$, $R_{GEN} = 6 \ \Omega$ Turn-Off Delay Time $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$,Turn-Off Fall Time $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$,Total Gate Charge $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$,	Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ 1Gate Threshold Voltage $I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$ 1Temperature Coefficient $V_{DS} = 10 \ V$, $I_D = 6.5 \ A$ 20Static Drain-Source $V_{GS} = 10 \ V$, $I_D = 6.5 \ A$, $T_J=125^{\circ}C$ 20On-Resistance $V_{GS} = 10 \ V$, $V_{DS} = 5 \ V$ 20Porvard Transconductance $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$ 20CharacteristicsInput Capacitance $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$ Reverse Transfer Capacitance $V_{DS} = 15 \ V$, $V_{GS} = 0 \ V$, $f = 1.0 \ MHz$ 1Turn-On Delay Time $V_{DS} = 15 \ V$, $I_D = 1 \ A$, $V_{GS} = 10 \ V$, $R_{GEN} = 6 \ \Omega$ 1Turn-Off Delay Time $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$, $V_{SS} = 10 \ V$, $R_{GEN} = 6 \ \Omega$ 1Turn-Off Fall Time $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$, $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$,1	Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \ \mu A$ 11.7Gate Threshold Voltage Temperature Coefficient $I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$ -4Static Drain-Source $V_{GS} = 10 \ V, I_D = 6.5 \ A$ 0.028On-Resistance $V_{GS} = 10 \ V, I_D = 6.5 \ A$, TJ=125°C0.044On-State Drain Current $V_{GS} = 10 \ V, V_{DS} = 5 \ V$ 20Forward Transconductance $V_{DS} = 5 \ V, I_D = 6.5 \ A$ 13CharacteristicsInput Capacitance $V_{DS} = 15 \ V, V_{GS} = 0 \ V, f = 1.0 \ MHz$ 460Output Capacitance $V_{DS} = 15 \ V, V_{GS} = 0 \ V, f = 1.0 \ MHz$ 115Reverse Transfer Capacitance $V_{DD} = 15 \ V, I_D = 1 \ A, V_{GS} = 10 \ V, R_{GEN} = 6 \ \Omega$ 8Turn-On Delay Time $V_{DS} = 10 \ V, R_{GEN} = 6 \ \Omega$ 17Turn-Off Delay Time $V_{DS} = 5 \ V, I_D = 6.5 \ A, J_T$ 13Total Gate Charge $V_{DS} = 5 \ V, I_D = 6.5 \ A, J_T$ 5	Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ 11.73Gate Threshold Voltage Temperature Coefficient $I_D = 250 \ \mu A$, Referenced to 25° C-4Static Drain-Source On-Resistance $V_{GS} = 10 \ V$, $I_D = 6.5 \ A$ $V_{GS} = 10 \ V$, $I_D = 6.5 \ A$, $T_J=125^{\circ}$ C0.0280.038 0.044On-Resistance $V_{GS} = 10 \ V$, $I_D = 5.5 \ A$ 0.0280.0440.060 0.040On-State Drain Current $V_{GS} = 10 \ V$, $V_{DS} = 5 \ V$ 20-Forward Transconductance $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$ 13- Characteristics 115Input Capacitance Reverse Transfer Capacitance $V_{DS} = 15 \ V$, $V_{GS} = 0 \ V$, f = 1.0 MHz460 Characteristics 45- Turn-On Delay Time Turn-Off Delay Time $V_{DD} = 15 \ V$, $I_D = 1 \ A$, $V_{GS} = 10 \ V$, $R_{GEN} = 6 \ \Omega$ 817Turn-Off Fall Time $V_{DS} = 5 \ V$, $I_D = 6.5 \ A$, $V_{CS} = 5 \ V$, $I_D = 6.5 \ A$, $V_{CS} = 7 \ V_{DS} = 5 \ V$ 57

FDS6630A

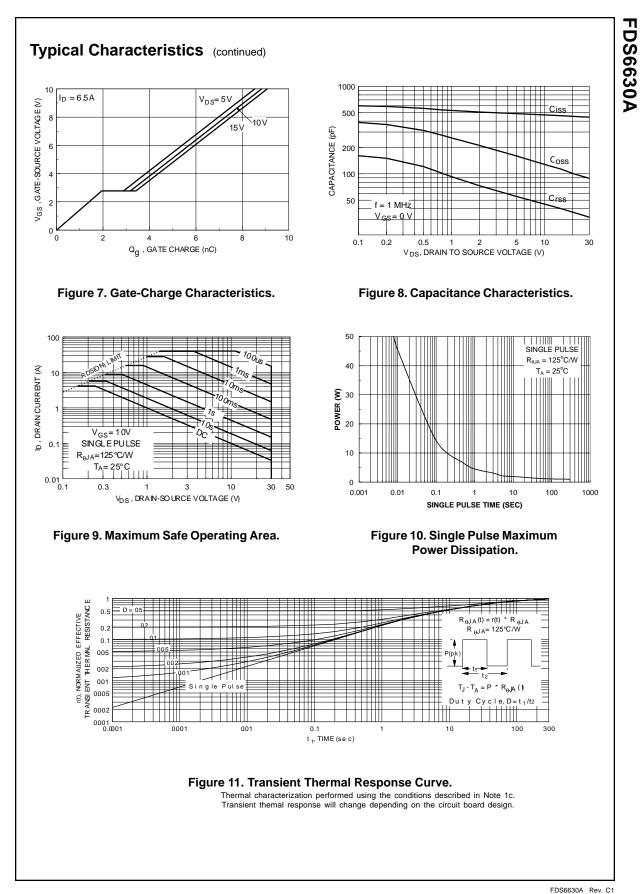
FDS6630A Rev. C1

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%



FDS6630A Rev. C1



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